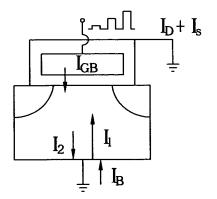


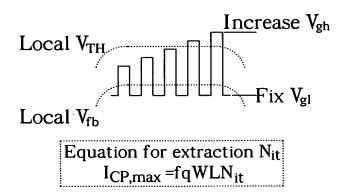
• Charge Pumping (CP) Setup



- $I_B = I_1 I_2$ =Recombination Current =CP Current ( $I_{CP}$ )
- I<sub>GB</sub> = Gate-Bulk Leakage

Fig. 1a





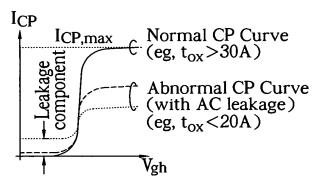


Fig. 1b



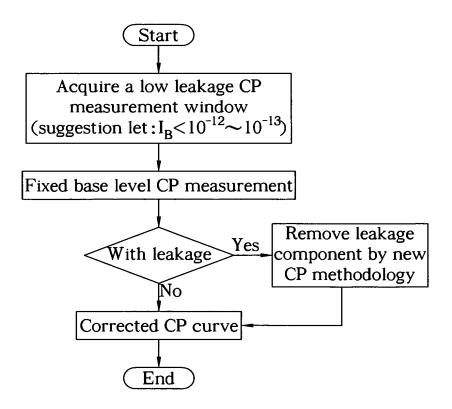
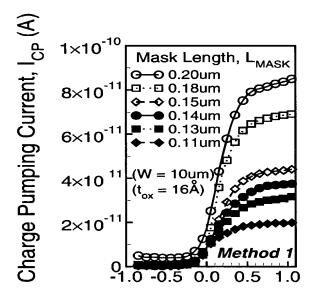


Fig. 1c





High Level Gate Voltage,  $V_{gh}$  (V)

Fig. 3



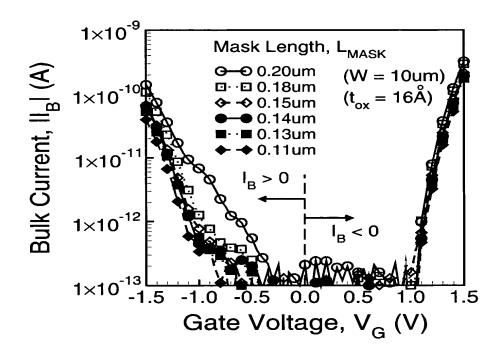


Fig. 4



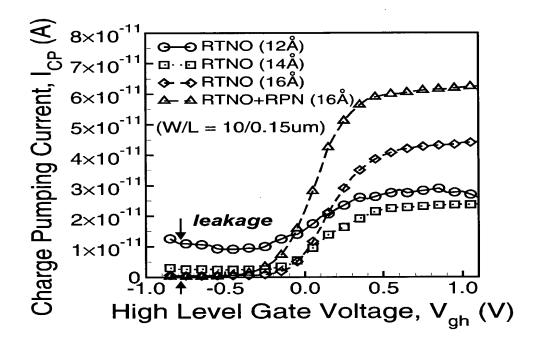


Fig. 5



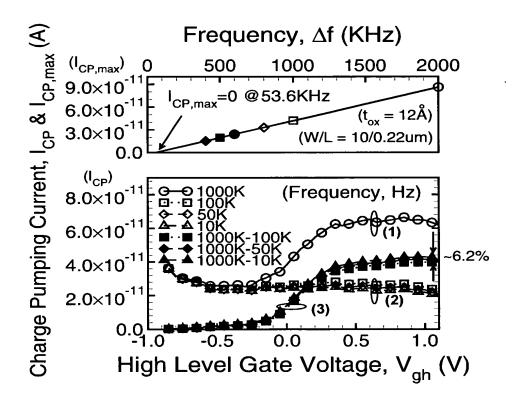


Fig. 6



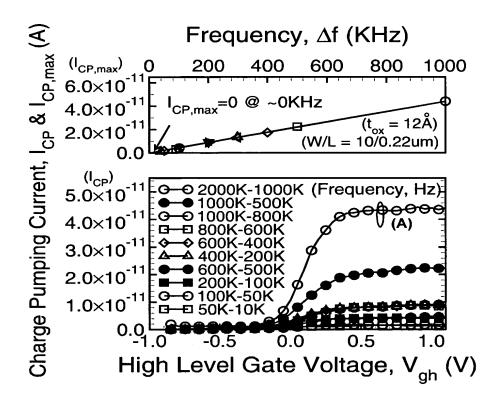


Fig. 7



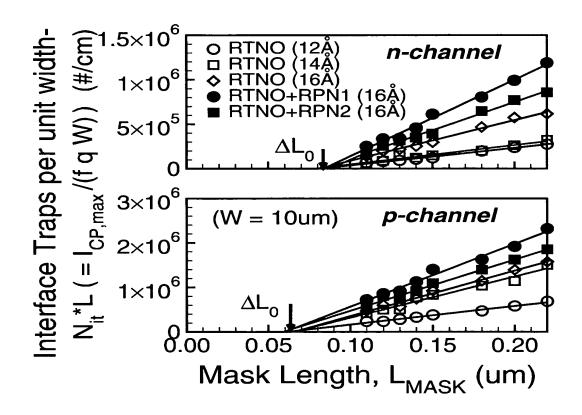


Fig. 9



(1 a) 
$$L_{MASK} = L_{gate} + 2 * \frac{\Delta L_1}{2} = L_{gate} + \Delta L_1$$
  
(1 b)  $L_{gate} = L_{eff} + 2 * \frac{\Delta L_2}{2} = L_{eff} + \Delta L_2$   
(1 c)  $\Delta L_0 \cong \Delta L_1 + \Delta L_2$   
(2 a)  $N_{ii,1,total} = N_{ii,11} + N_{ii,12}$   
(2 b)  $N_{ii,2,total} = N_{ii,21} + N_{ii,22}$   
(2 c)  $\Delta I_{CP,max} \propto \Delta N_{ii,total} = N_{ii,11} + N_{ii,12} ) - (N_{ii,21} + N_{ii,22} )$   
(1 if  $N_{ii,11} \approx N_{ii,21} )$   
(1 if  $N_{ii,11} \approx N_{ii,21} )$   
(1 if  $N_{ii,11} \approx N_{ii,21} )$ 

Table 1

Fig. 10